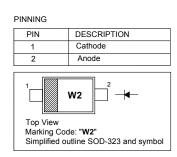
SILICON EPITAXIAL PLANAR DIODE

APPLICATIONS

• High speed switching



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	85	V
Reverse Voltage	V _R	80	V
Average Forward Current	Ι _Ο	100	mA
Peak Forward Current	I _{FM}	300	mA
Non-repetitive Peak Forward Current (t = 1 µs)	I _{FSM}	4	A
Junction Temperature	TJ	125	°C
Storage Temperature Range	T _{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 10 mA at I _F = 100 mA	V _F	0.8 1.2	V
Reverse Current at V _R = 80 V	I _R	0.1	μA
Capacitance between Terminals at $V_R = 0 V$, f = 1 MHz	CT	2	pF
Reverse Recovery Time at V _R = 6 V, I _F = 10 mA, R _L = 50 Ω	t _{rr}	3	ns







Dated : 07/04/2009

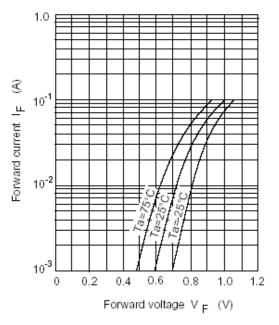


Fig.1 Forward current Vs. Forward voltage

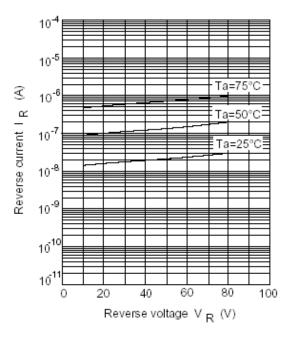


Fig.2 Reverse current Vs. Reverse voltage

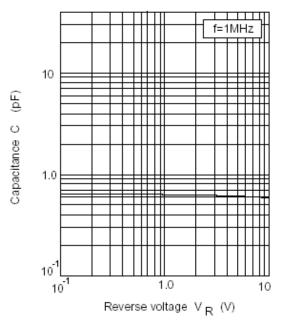


Fig.3 Capacitance Vs. Reverse voltage





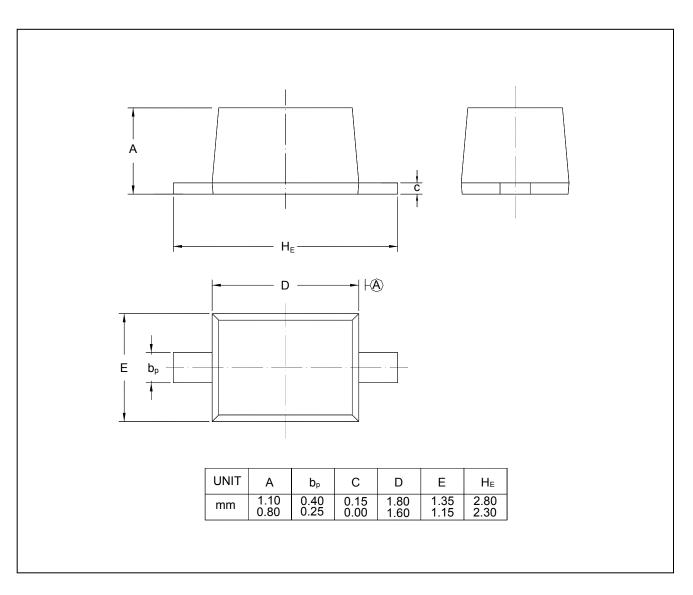
SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)

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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323









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